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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/671,608	(	09/29/2003	Tetsuo Ono	520.38979CX1 EXA VIN	8510
20457	7590	04/04/2006		EXAM	IINER
		RY, STOUT & KF	AUS, LLP	VINH	, LAN
1300 NORT SUITE 1800		TEENTH STREET		ART UNIT	PAPER NUMBER
ARLINGTO		22209-3873		1765	

DATE MAILED: 04/04/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
Office A 41	10/671,608	
Office Action Summary	Examiner	ONO ET AL.
	1>0	Art Unit
The MAILING DATE of this communication ap	pears on the cover sheet with	1765
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION.  Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication.  If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period to Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	Y IS SET TO EXPIRE 3 MOI 136(a). In no event, however, may a reply by within the statutory minimum of thirty (3	NTH(S) FROM  y be timely filed  30) days will be considered timely
Status		· · · · · · · · · · · · · · · · · · ·
1) Responsive to communication(s) filed on 10 Fe 2a) This action is FINAL. 2b) This 3) Since this application is in condition for allowan closed in accordance with the practice under E Disposition of Claims	action is non-final.	, prosecution as to the merits is 1, 453 O.G. 213.
4) Claim(s) 10,12 and 21-26 is/are pending in the 4a) Of the above claim(s) is/are withdraw 5) Claim(s) 10,12,21,22,24 and 25 is/are allowed. 6) Claim(s) 23,26 is/are rejected.	application.  n from consideration.  .	
7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or	olootis	
Application Papers	election requirement.	
1		,
9) The specification is objected to by the Examiner.	•	
10) The drawing(s) filed on is/are: a) accep	oted or b) objected to by the	e Examiner
Replacement drawing sheet(s) including the correction  11) The oath or declaration is objected to by the Exam	n is required if the drawing(s) is o	objected to. See 37 CFR 1.121(d)
- Julie Exam	miner. Note the attached Offic	ce Action or form PTO-152.
1 Hority under 35 0.S.C. § 119		
<ul> <li>12) Acknowledgment is made of a claim for foreign print a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents he</li> <li>2. Certified copies of the priority documents he</li> </ul>	ave been received.	·
<ul> <li>2. Certified copies of the priority documents hat 3. Copies of the certified copies of the priority application from the International Bureau (P*</li> <li>* See the attached detailed Office action for a list of the second company of the priority application from the International Bureau (P*</li> </ul>	CCT Dute 47.00 W	ed in this National Stage
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application from the International Bureau (P * See the attached detailed Office action for a list of the	PCT Rule 17.2(a)).  the certified copies not receive  4)  Interview Summary Paper No(s)/Mail Di	/ed in this National Stage ed.

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#### **DETAILED ACTION**

### Response to Amendment/Argument

1. The applicants argument that the teachings of the applied references would have neither disclosed nor would have suggested wherein a mixing rate of the adhesive gas to be mixed with the halogen gas ranges from 0.5%-50% is moot in view of the newly cited reference of Gutsche et al (US 6,177,353). Thus, the indication of allowable subject matter in claim 20 has been withdrawn in view of newly found reference of Gutsche et al (US 6,177,353)

### Claim Rejections - 35 USC § 112

2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 23 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 23 recites the limitation "said processing steps". There is insufficient antecedent basis for this limitation in the claim.

# Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claim 26 is rejected under 35 U.S.C. 103(a) as being unpatentable over Ye et al (US 6,080,529) in view of Gutsche et al (US 6,177,353)

Ye discloses a method of etching wherein a substrate where a mask layer without containing carbon as a major component formed on the layer to be processed is laid on a support pedestal/sample board in a vacuum container (col 11, lines 30-35; fig. 5), plasma is generated inside said vacuum container (col 10, lines 64-66), radio frequency bias voltage is applied on said pedestal/sample board (col 10, lines 55-56) and plasma treatment is provided by periodic on-off control radio frequency bias voltage applied on said pedestal/sample board (col 16, lines 60-65), wherein the plasma consists of a mixture of chlorine and BCl3/halogen gas and CH4/methane/carbon hydride/adhesive gas (col 17, lines 27-34)

Unlike the instant claimed invention as per claim 26, Ye fails to disclose that a mixing rate of the adhesive gas to the halogen gases ranges from 0.5-50%

Gutsche discloses a method of plasma etching comprises the step of etching using a mixture of chlorine and BCl3/halogen gas and CH4/methane/carbon hydride/adhesive, wherein the mixing rate of CH4/adhesive gas to the halogen gases ranges from 0-20% (col 7, lines 1-7)

Hence, one skilled in the art at the time the invention was made would have found it

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obvious to modify Ye etching gas mixture by using a mixing rate of the adhesive gas to the halogen gases in the ranges as taught per Gutsche because Gutsche discloses that the percentage of CH4 addition to the total flow of Cl2 and BCl3 is preferably between about 2-8% (col 7, lines 6-8)

#### Allowable Subject Matter

5. Claims 10, 12, 21-22, 24-25 allowed.

Claim 23 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 112, 2nd paragraph, set forth in this Office action.

The following is an examiner's statement of reasons for allowance:

Regarding claims 21-22, the cited prior art of record fails to disclose or suggest a surface processing method of a sample comprises a step of etching said n-type polycrystalline siliçon and said p-N type polycrystalline silicon by introducing mixed gas containing fluorine and oxygen into said vacuum container while applying periodically on-off controlled radio frequency bias voltage, in combination with the rest of the limitations of claims 21-22

Regarding claims 24-25, the applicants have presented a persuasive argument, see page 10 of the response filed on 2/10/2006 that the cited prior art of record fails to disclose or suggest a surface processing method of a sample comprises a limitation of wherein a percentage of on-period accounts for 5 to 60% in a cycle of on-off control of said radio frequency voltage, and said sample is treated by said plasma, in combination with the rest of the limitations of claims 24-25

#### Conclusion

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov.

LV

April 03, 2006